

MEMORY CELL STRINGS

Abstract of the Disclosure

A data storage device comprising a first memory cell string that includes at least a first magnetic random access memory (MRAM) cell coupled to a second MRAM cell and a circuit coupled to a node between the first MRAM cell and the second MRAM cell is provided. The circuit is configured to detect a voltage change at the node in response to a voltage being provided to the memory cell string and in response to a write sense current being applied across the first MRAM cell.